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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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10/751,091

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EXAMINER

WARTALOWICZ, PAUL A

ART UNIT

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1793

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PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary	Application No. 10/751,091	Applicant(s) MOECKLY ET AL.	
	Examiner PAUL A. WARTALOWICZ	Art Unit 1793	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 01 May 2008.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-21 and 59-64 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-21 and 59-64 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____ |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08) | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

Response to Arguments

Applicant's arguments with respect to claims 1-21 have been considered but are moot in view of the new ground(s) of rejection.

Applicant argues that Hunt discloses only a deposited barrier.

However, Hunt discloses an ion-etched barrier as described in the rejection below.

The references that have been traversed for being published after the effective date have been withdrawn from the rejections.

Applicant submitted an affidavit that explains that the Harada paper differs from the instant application in that the technique for producing the barrier layer is different.

However, the Harada paper is not relied upon to teach the properties of the barrier layer. The Hunt and Jia papers are relied upon to teach this limitation.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-5, 7- 21, and 59-64 are rejected under 35 U.S.C. 103(a) as being unpatentable over Harada et al. ("Fabrication of All-High-Tc Josephson Junction . . .") in view of Chan (U.S. 5,892,243) and either one of Hunt et al. ("High Temperature

Superconductor Josephson Weak Links”) or Jia et al. (Effect of chemical and ion-beam...).

Figure 2 of Harada shows a Josephson junction having a crystalline substrate MgO, a YBCO electrode formed on and epitaxial to the substrate (page 1389, column 1, lines 4-7), an insulator a-YSZ, a barrier comprising a plasma-treated surface of the YBCO (page 1387, column 1, second paragraph), and a YBCO counter-electrode formed directly on and epitaxial to the barrier.

Chan teaches with respect to the cover figure to form insulator 48 epitaxially on YBCO 46 (column 6, lines 25-32).

It would have been obvious to form an epitaxial insulator on the Harada device instead of a-YSZ, in order to obtain the higher quality crystalline material obtained by epitaxial growth.

With respect to claims 2-4, a process limitation carries weight in a claim drawn to a product only when distinct structure is produced by the process. *In re Thorpe*, 227 USPQ 964 (Fed. Cir. 1985). There is no evidence of record to show that the process steps recited would necessarily give rise to a barrier layer distinct from that of Harada.

With respect to claim 5, both of the Harada YBCO layers have their c-axis perpendicular to the substrate (page 1389, column 1, lines 4-7). Therefore the top plane of the lower YBCO must be an a-b plane, and a junction is formed in that plane.

With respect to the layer in-between the superconducting layers wherein the barrier layer is produced by ion-milling the superconducting layer, Hunt teaches the claimed process limitations (pages 3 and 4).

Jia teach forming barrier layers by ion-etching a superconductor (pg 3635, Fig 2).

Therefore, it would have been obvious to one of ordinary skill in the art to provide a non-superconducting, ion modified surface layer of a superconducting oxide in Harada in order to provide a barrier layer between two superconducting oxides as taught by Hunt or Jia.

Harada et al. fail to teach the claimed $I_c R_n$ product.

However, Hunt teach that it is known for YBCO with microbridges to exhibit an $I_c R_n$ product of around 1.03 mV at a temperature of 4.2 K and an $I_c R_n$ product of around 450 μ V a temperature of 77 K (pg 4).

Therefore, it would have been obvious to one of ordinary skill in the art at the time applicant's invention was made to provide the claimed $I_c R_n$ product in Harada because the fabrication method for making YBCO devices exhibiting the claimed $I_c R_n$ product are known as taught by Hunt.

With respect to claims 63 and 64, it appears that the process of making the junctions is substantially similar to the claimed invention such that the properties of the junctions of the prior art are substantially similar to those of the claimed invention.

Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Harada et al. ("Fabrication of All-High-T_c Josephson Junction . . .") in view of Chan (U.S. 5,892,243) and Laibowitz et al. ("All high T_c edge junctions and SQUIDS").

Laibowitz et al. teaches at the bottom of column 1 of page 686 that transport along the a-b plane direction has a longer coherence length and higher current density.

It would have been obvious to arrange a junction perpendicular to the a-b plane for these reasons. The device of Harada in figure 2 has a perpendicular portion of the junction that would be perpendicular to the a-b plane, because the c direction is perpendicular to the MgO substrate.

Claims 13 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Harada et al. ("Fabrication of All-High-T_c Josephson Junction . . .") in view of Chan (U.S. 5,892,243) and Laibowitz et al. ("All high T_c edge junctions and SQUIDS") and Satoh et al. ("Effect of Lanthanum Doping of YBaCuO...").

Harada et al. fail to teach the claimed $I_c R_n$ product.

Satoh teach a method of making YBCO (pg 1) wherein lanthanum doped YBCO produces a higher $I_c R_n$ product than that of pure YBCO (pp. 2, 3).

Therefore, it would have been obvious to one of ordinary skill in the art at the time applicant's invention was made to provide a higher $I_c R_n$ product than that of pure YBCO in Harada et al. because it is known to dope YBCO with lanthanum in order to obtain high $I_c R_n$ product.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to optimize an $I_c R_n$ product, since it has been held that discovering an optimum value or a result effective variable involved only routine skill in the art. In re Boesch, 617 F.2nd 272, 205 USPQ 215 (CCPA 1980). The artisan would have been motivated to optimize an $I_c R_n$ product by the reasoning that higher $I_c R_n$ product enables annealing at higher temperatures for longer durations as taught by Satoh.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to PAUL A. WARTALOWICZ whose telephone number is (571)272-5957. The examiner can normally be reached on 8:30-6 M-Th and 8:30-5 on Alternate Fridays.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Stanley Silverman can be reached on (571) 272-1358. The fax phone

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number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Paul Wartalowicz
August 13, 2008

/Steven Bos/
Primary Examiner
A.U. 1793